Control of Magnetism with Oxide Hybrid Structures

Siming Wang

University of California San Diego

Magnetism

DEPARTMENT OF ENERGY · UNITED STATES OF AMERICA

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Oxide

AFOSR
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FA9550-12-1-0381

Acknowledgement

Prof. Ivan K. Schuller
Principal Investigator

Prof. Jose de la Venta
Thin Film, Magnetism

Dr. Thomas Saerbeck
Diffraction, Magnetism

Dr. Juan Gabriel Ramirez
Thin Film, Magnetism (FMR)

Ilya Valmianski
AFM, SEM, Fabrication
ivalmian@ucsd.edu

Siming Wang
Thin Film, Simulation,
Fabrication

Outline

- ***Introduction***
  - – Review Control of Magnetism
  - – Phase Transition in Vanadium Oxide (VO_x)

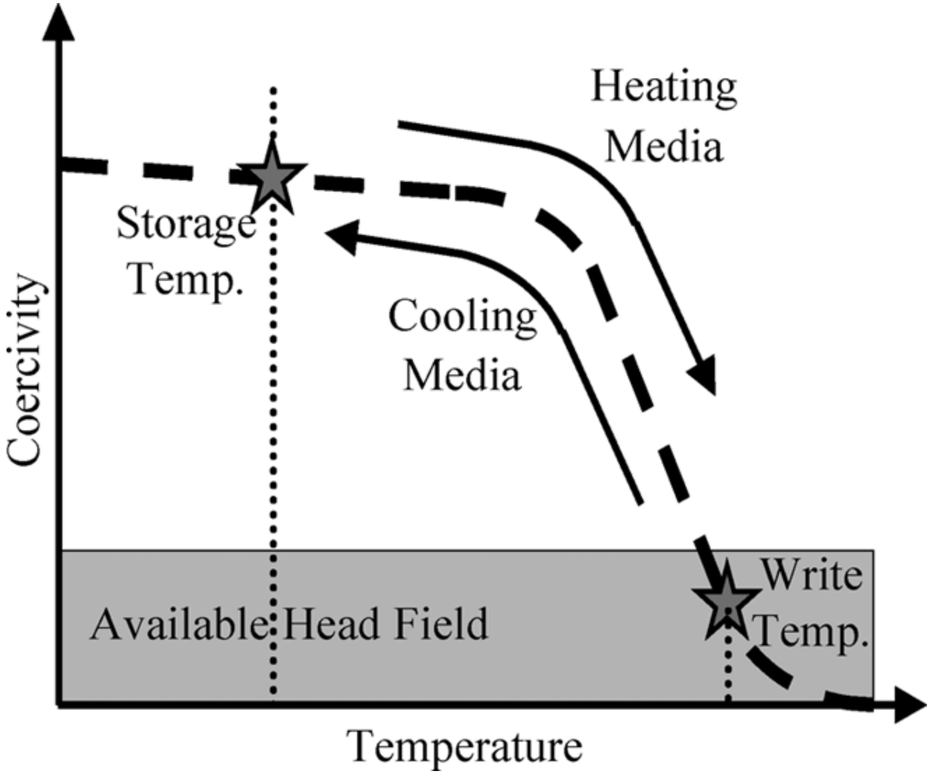
- ***Control of Magnetism with VO_x/FM***
  - – Tuning with Magnetostrictive Effect

- ***Coercivity Enhancement in V_2O_3/Ni***
  - – Competing Length Scales on Nanoscale

- ***Summary and Outlook***

Control of Magnetism

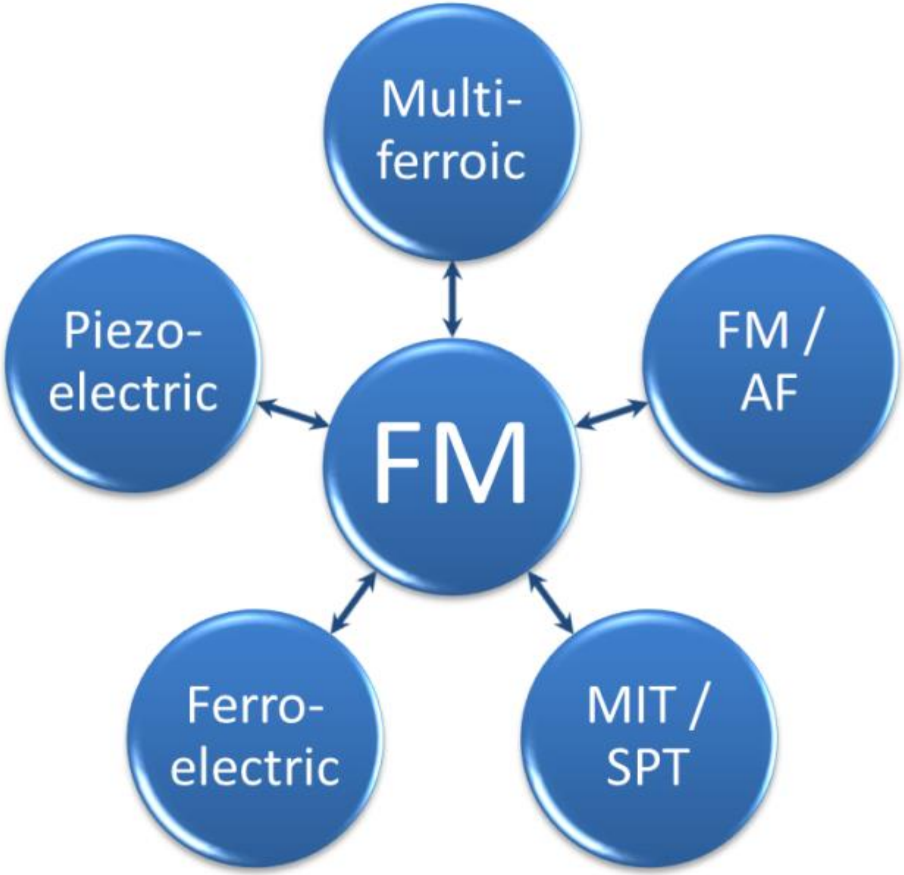
Heat Assisted Magnetic Recording (HAMR)



- Microwave Assisted
- Acoustic Phonon Assisted
- Ultrafast Laser Induced

M. H. Kryder, E. C. Gage, T. W. McDaniel, W. A. Challener, R. E. Rottmayer, G. Ju, Y.-T. Hsia, and M. Fatih Erden, Proc. IEEE **96**, 1810 (2008)

“Sun-Wheel” of Oxide Hybrid Structures



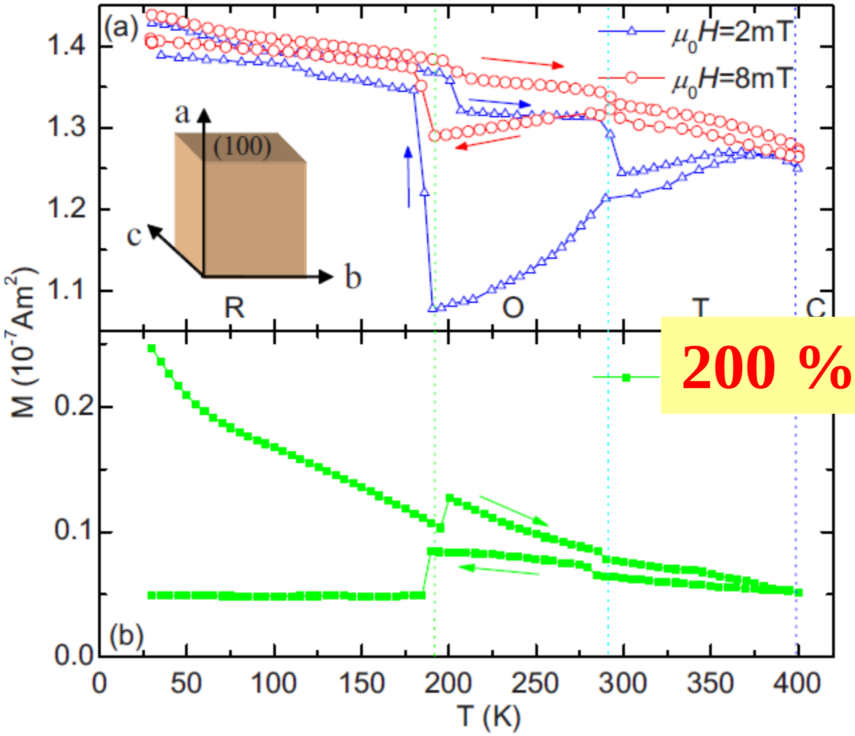
FM: Ferromagnetic
AF: Antiferromagnetic

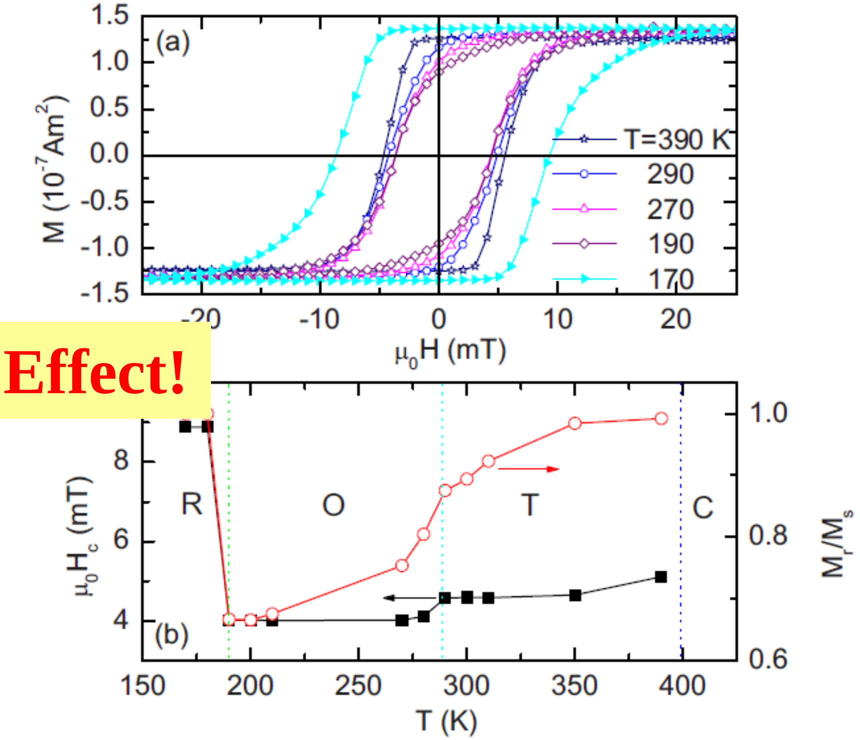
MIT: Metal Insulator Transition
SPT: Structural Phase Transition

T. Saerbeck, J. de la Venta, S. Wang, J. G. Ramirez, M. Erekhinsky, I. Valmianski, I. K. Schuller, J. Mater. Res., Invited Review (2014)

Control of Magnetism with SPT

$BaTiO_3$ /Fe Bilayer: Control through Interface Strain Coupling





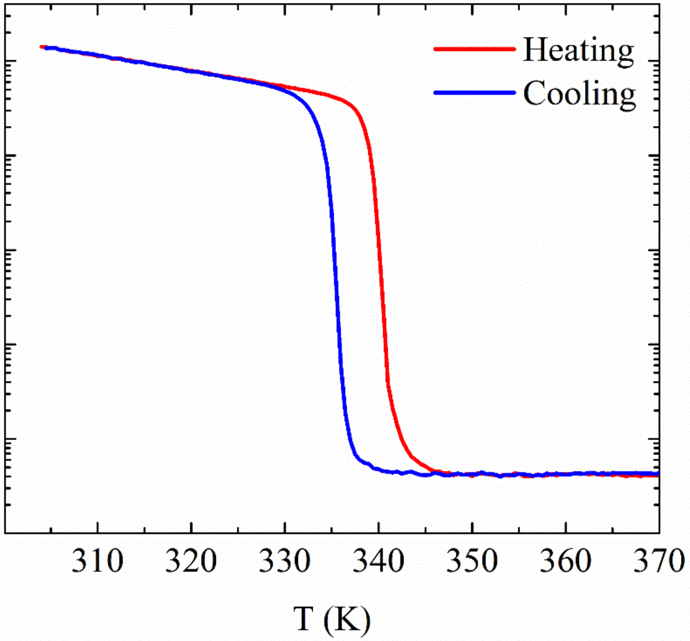
200 % Effect!

S. Sahoo *et al.*, Phys. Rev. B **76**, 092108 (2007)

Phase Transition in VO_2

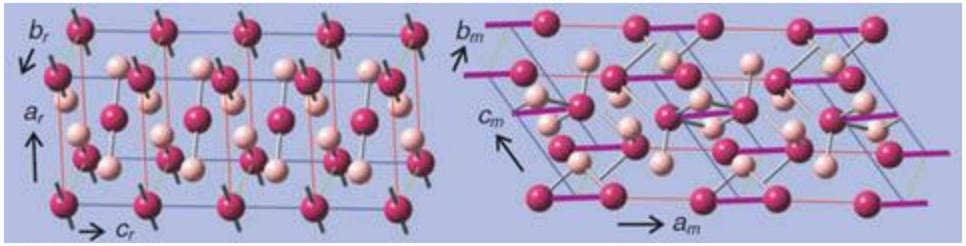
MIT

SPT



$T_C = 340$ K

High-T Rutile **Low-T Monoclinic**



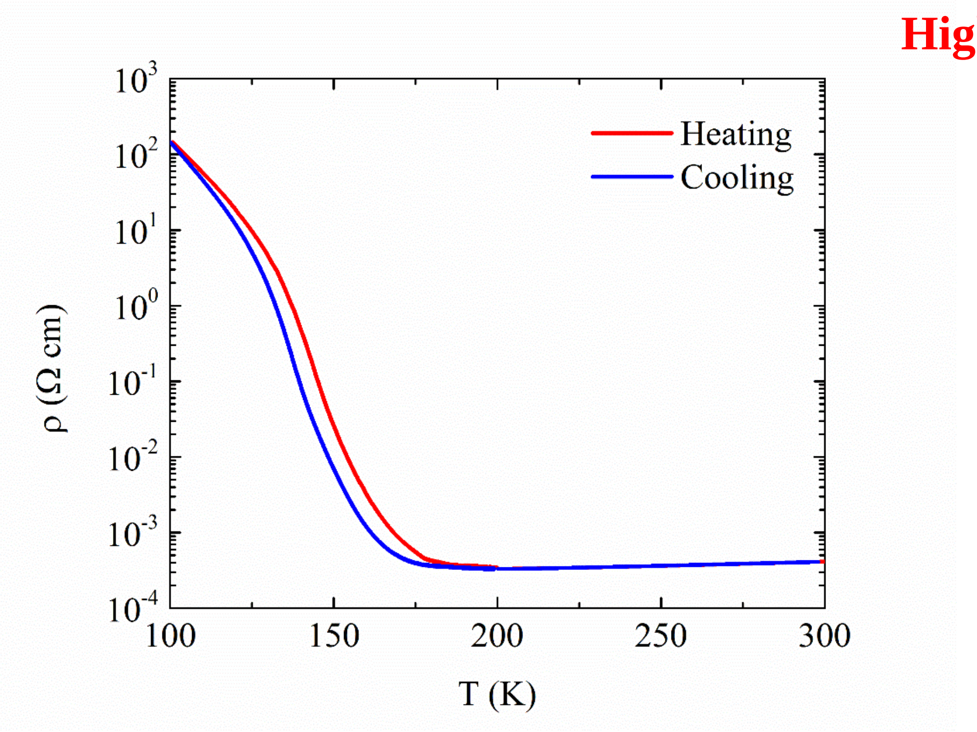
P. Baum *et al*., Science **318**, 788 (2007)

~ 1 % Lattice Distortion

~ 1 % Volume Change

Phase Transition in V_2O_3

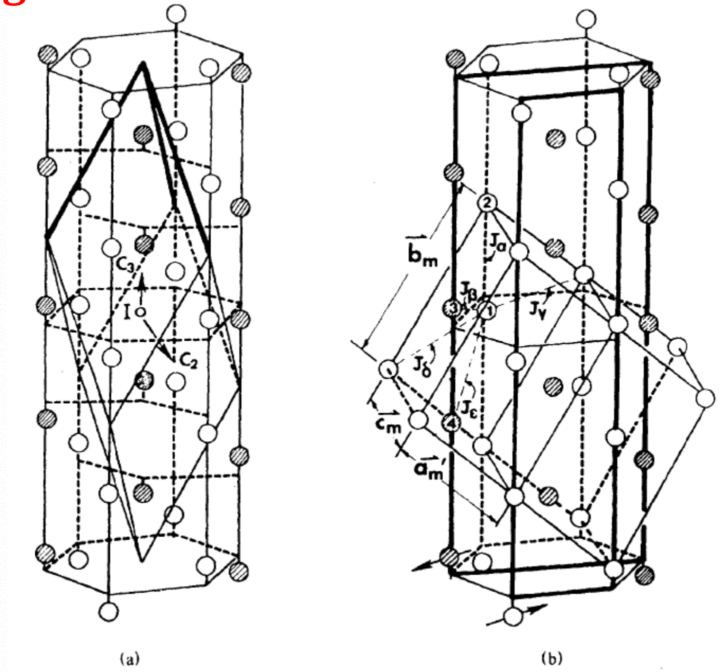
MIT



$T_C = 150 – 165$ K

SPT

High-T Rhombohedral **Low-T Monoclinic**



R. E. Word *et al.*, Phys. Rev. B **23**, 3533 (1981)

~ 1 % Lattice Distortion

~ 1 % Volume Change

Why VO_x?

- First Order Phase Transition

Abrupt Structural Change in **Narrow** Temperature Range

- Choice of Transition Temperatures

$T_C(VO_2)$ = 340 K, $T_C(V_2O_3)$ = 150 – 165 K

- Multiple Driving Forces to Induce SPT

Temperature, Voltage/Current, Light, Gating, Pressure, etc.

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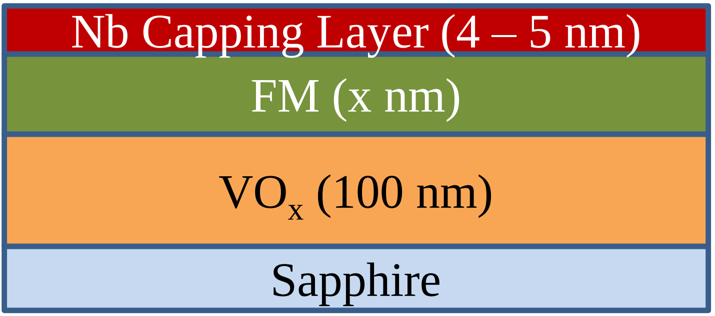
  - Competing Length Scale on Nanoscale

- ***Conclusions***

VO_2 / Ni

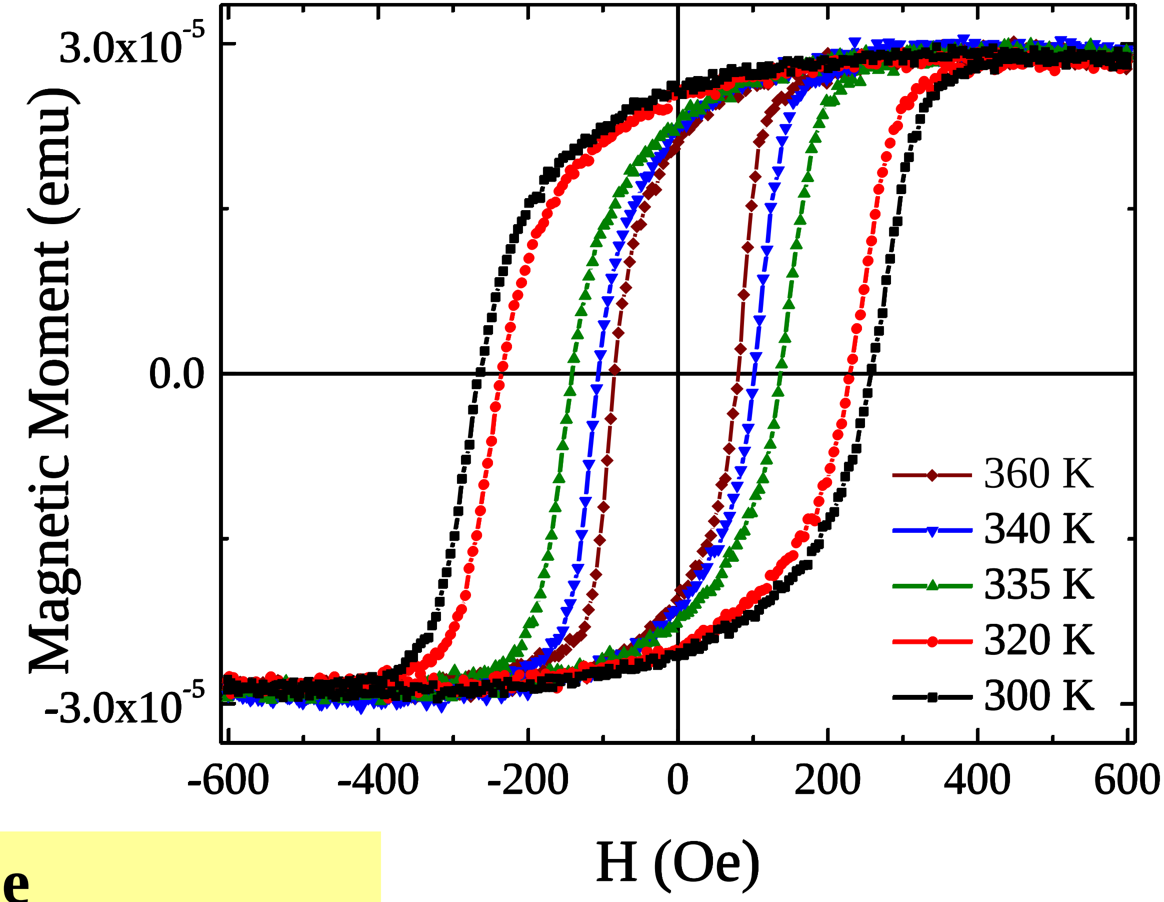


Nb Capping Layer (4 – 5 nm)

FM (x nm)

VO_x (100 nm)

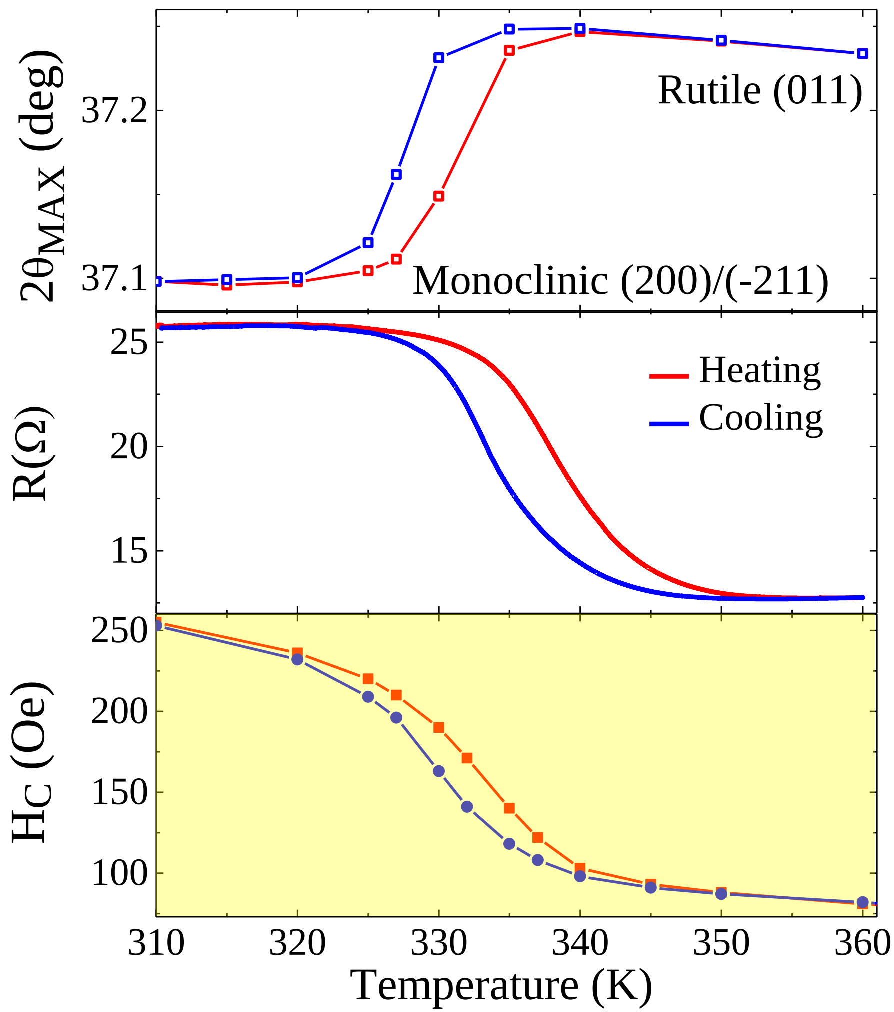
Sapphire



100 nm VO_2 / 10 nm Ni

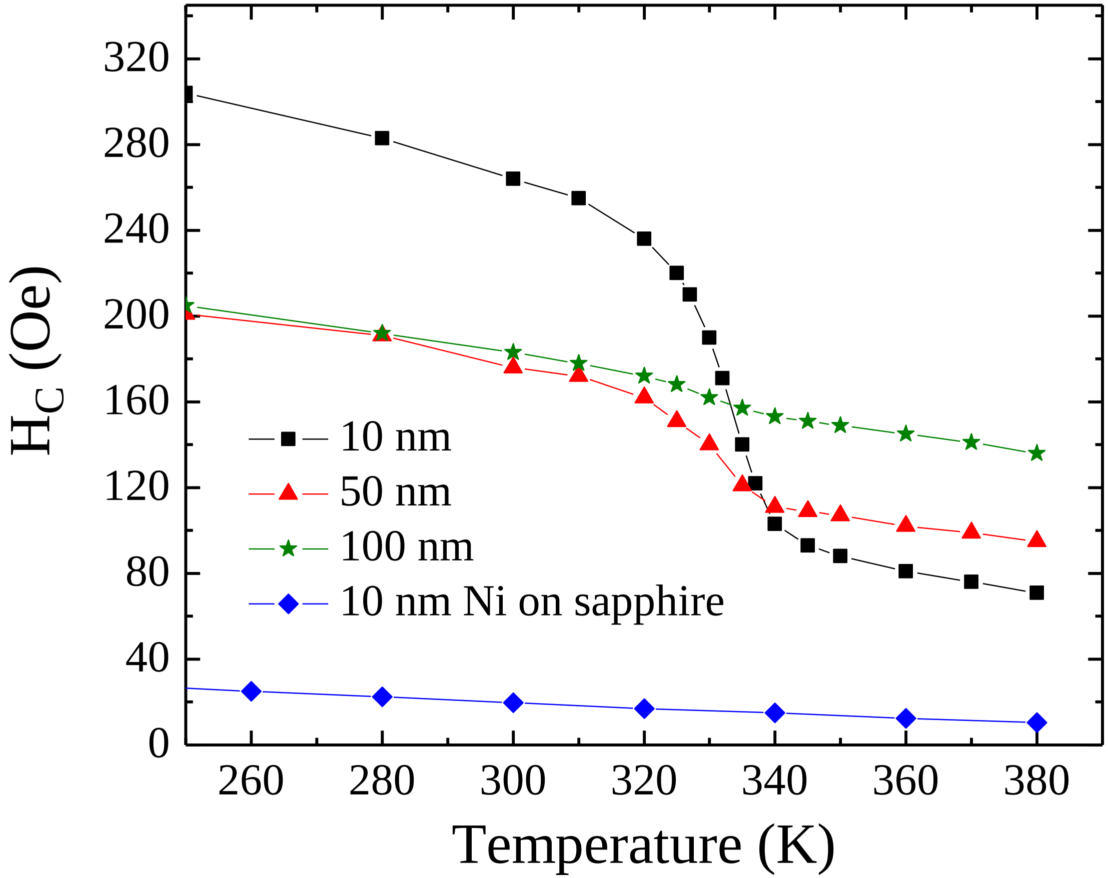
200 % Coercivity Change
across VO_2 Phase Transition at 340 K

Correlation: Phase Transition & Magnetism



Temperature Dependence & Thermal Hysteresis of H_C Coincide with MIT & SPT of VO_2

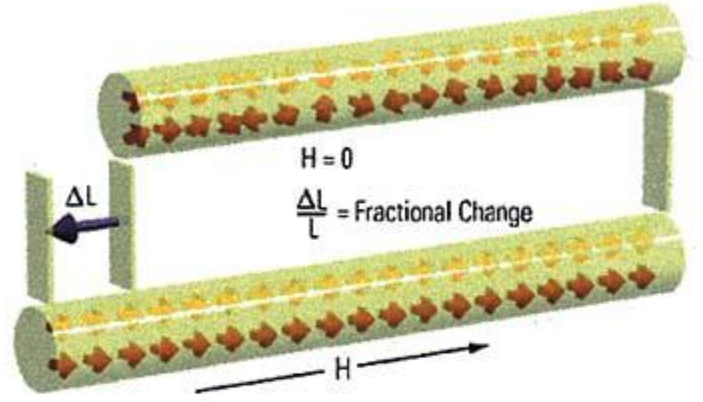
Ni Thickness Dependence



Effect Reduces as Ni Thickness Increases ➡ **Interface Effect**

Magnetostriction

Change of Dimensions in the Applied Field Direction

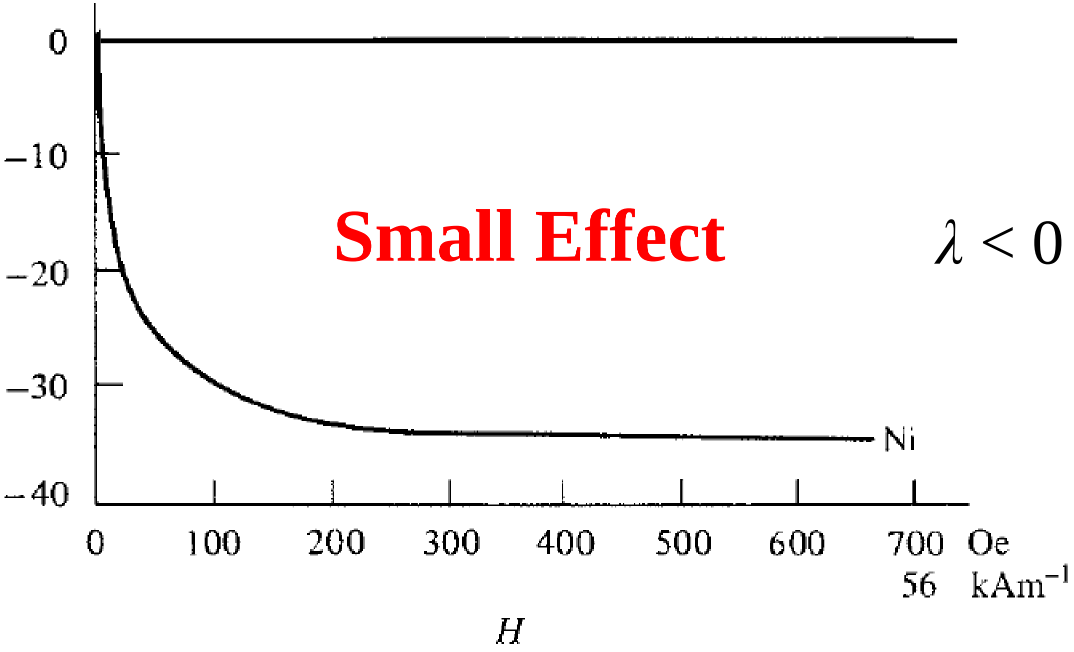


Magnetostriction Coefficient $\lambda = \frac{\Delta L}{L}$

$\lambda < 0$ Contracts when Magnetized
$\lambda > 0$ Elongates when Magnetized

Polycrystalline Ni λ

(10^{-6})



Small Effect

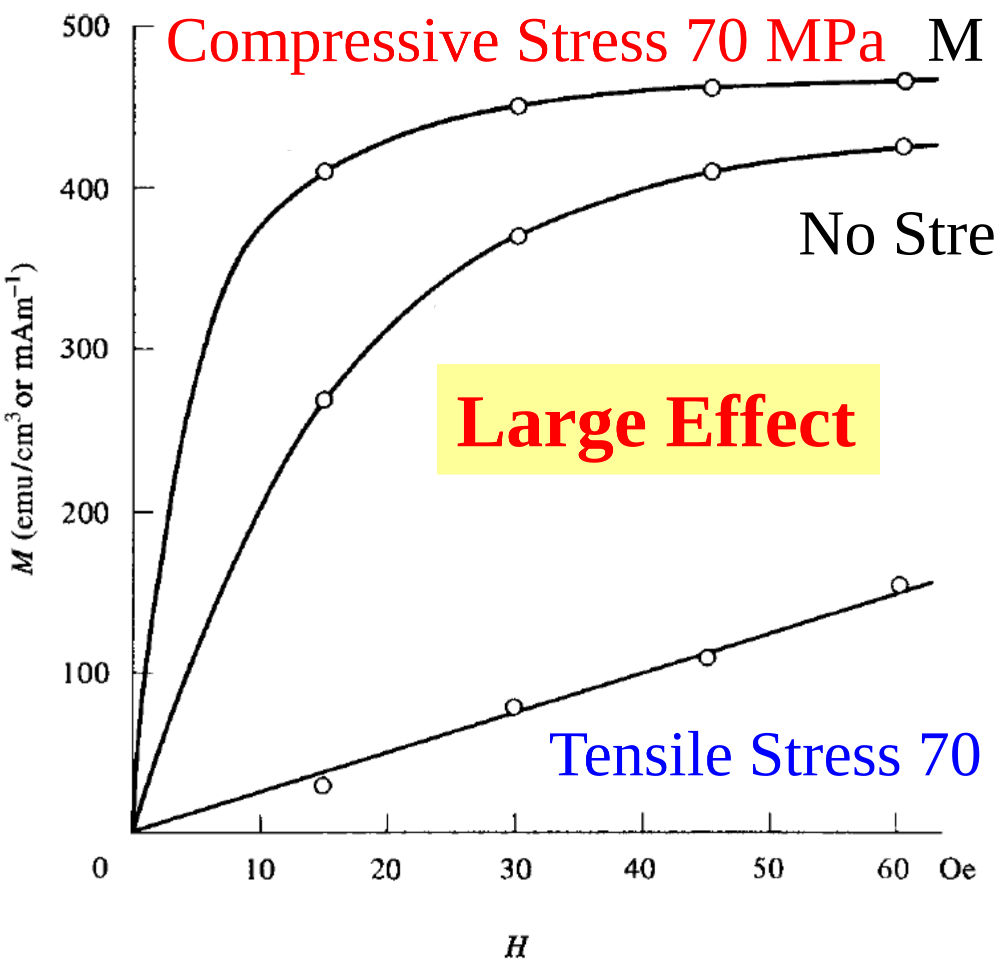
$\lambda < 0$

B. D. Cullity and C. D. Graham. Introduction to Magnetic Materials

Inverse Magnetostriction

Change of Magnetization due to Applied Stress

Polycrystalline Ni



Compressive Stress 70 MPa M ↑

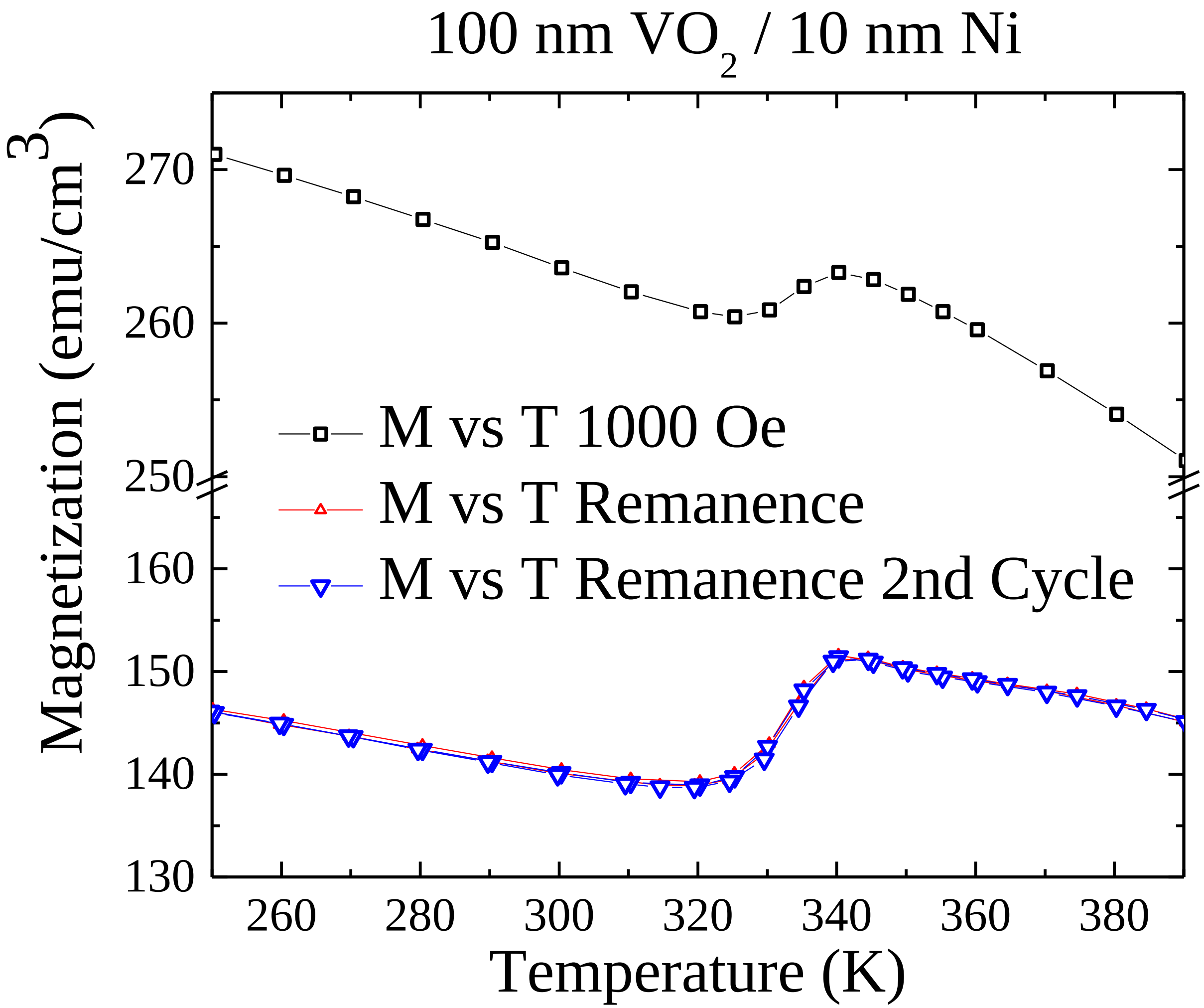
No Stress

Large Effect

Tensile Stress 70 MPa M ↓

B. D. Cullity and C. D. Graham. Introduction to Magnetic Materials

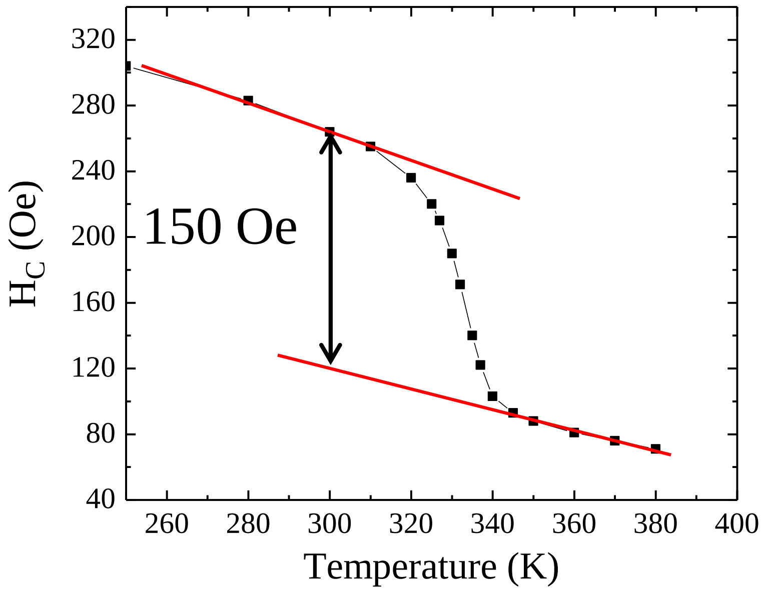
Magnetization vs. Temperature



Magnetic Domain Dynamics

Stress Anisotropy

100 nm VO_2 / 10 nm Ni



Stress Anisotropy Field

$$H_{K\sigma} = \frac{3\lambda\sigma}{M_S}$$

M_S = 470 emu/cm^3

$\lambda = -34 \times 10^{-6}$ Polycrystalline Ni

➡ **σ ~ 59 MPa**

Stress Measured in VO_2 Films **σ ~ 400 MPa**

B. Viswanath *et al.*, Scr. Mater. **64**, 490 (2011)

Tailoring the Effect

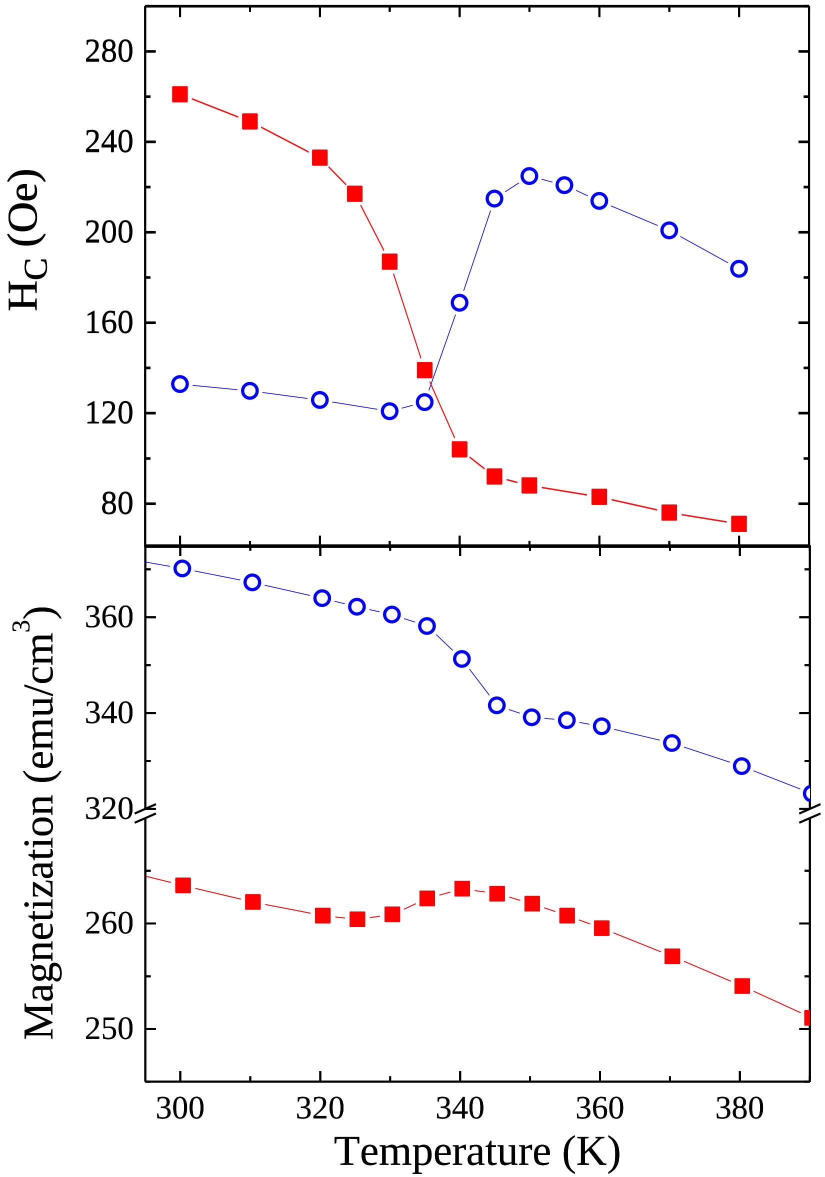
- Ni Deposited at 420 K

→ VO_2 Rutile

- Ni Deposited at RT

→ VO_2 Monoclinic

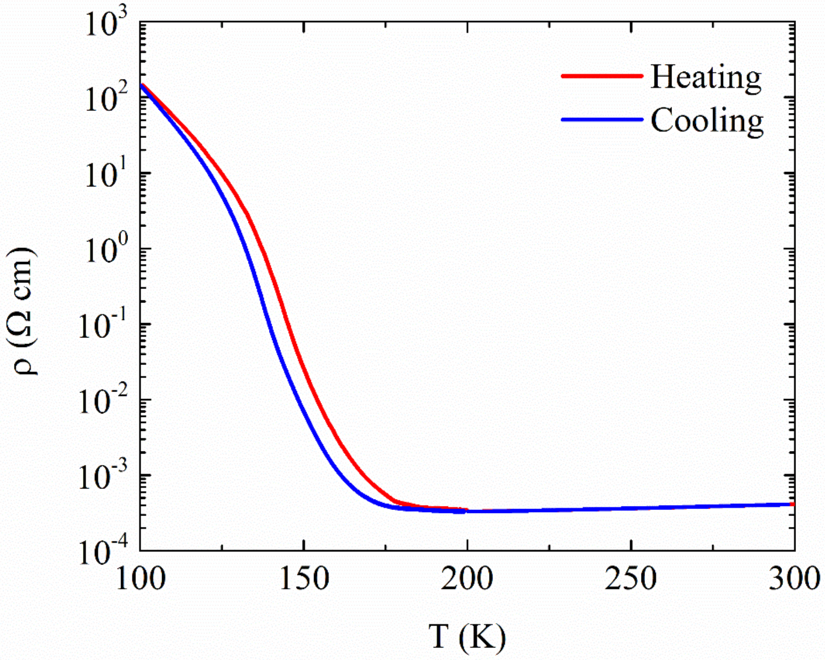
Reverse the Effect by Selecting the Deposition Temperatures, i.e. VO_2 Structures



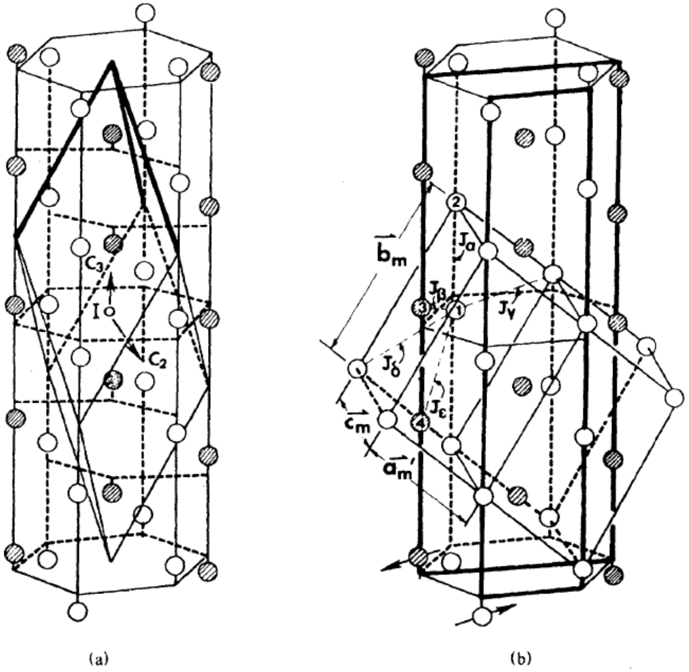
Phase Transition in V_2O_3

MIT

SPT



High-T Rhombohedral **Low-T Monoclinic**



R. E. Word *et al.*, Phys. Rev. B **23**, 3533 (1981)

T_C = 150 – 165 K

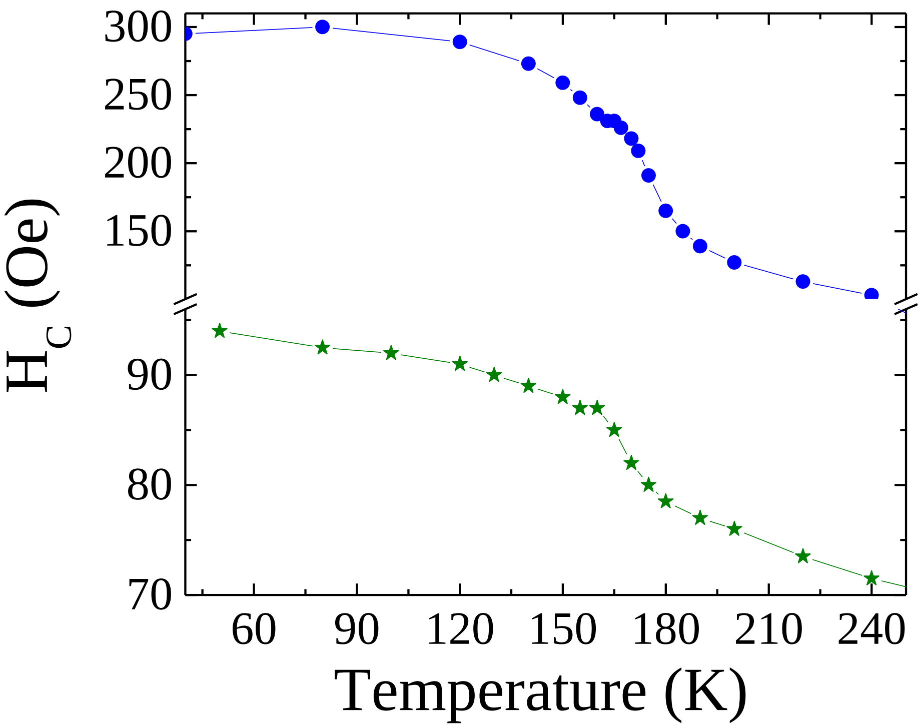
~ 1 % Lattice Distortion

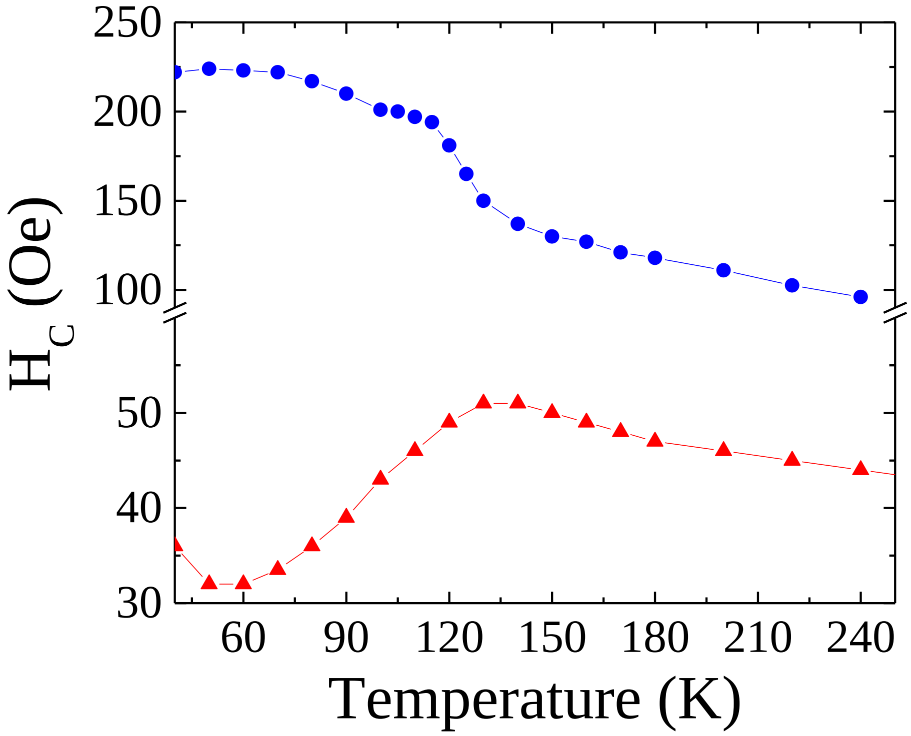
~ 1 % Volume Change

V_2O_3 / FM: Generalization

100 nm V_2O_3 | 10 nm Ni
10 nm Co

100 nm V_2O_3 | 10 nm Ni
10 nm Fe





- Fe & Co Smaller Effect ⬅ Smaller $\frac{\lambda}{M_S}$
- Fe Inverse Effect ⬅ $\lambda_{Fe} > 0$

$$H_{K\sigma} = \frac{3\lambda\sigma}{M_S}$$

Control of Magnetism with VO_x/FM

- Control **Coercivity** & **Magnetization** with **SPT** of VO_x
- Interface Effect – **Reduces with Increasing FM Thickness**
- Tuning with Stress – **Choose Deposition Temperatures**
- Tuning with FM – **Choose λ & M_s**

J. de la Venta, S. Wang, J. G. Ram ŕez, and Ivan K. Schuller, Appl. Phys. Lett. **102**, 122404 (2013)
T. Saerbeck, J. de la Venta, S. Wang, J. G. Ramirez, M. Erekhinsky, I. Valmianski, I. K. Schuller, J. Mater. Res., Invited Review (2014)
I. K. Schuller, J. de la Venta, S. Wang, J. G. Ramirez, M. Erekhinsky, and A. Sharoni. Magnetic and Electrical Control of Engineered Materials. United States Patent 61/915,715, Issued December 13, 2013

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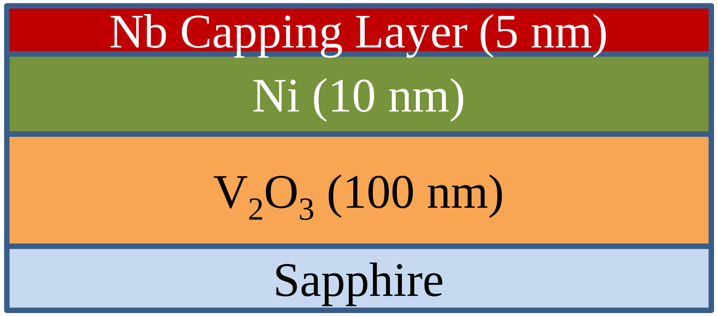
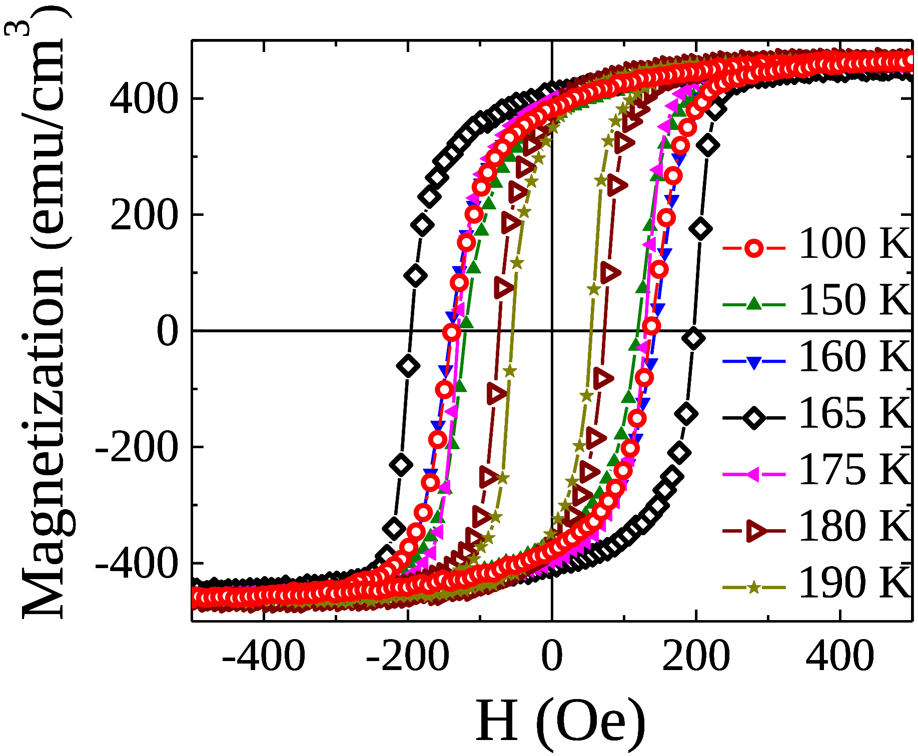
- ***Conclusions***

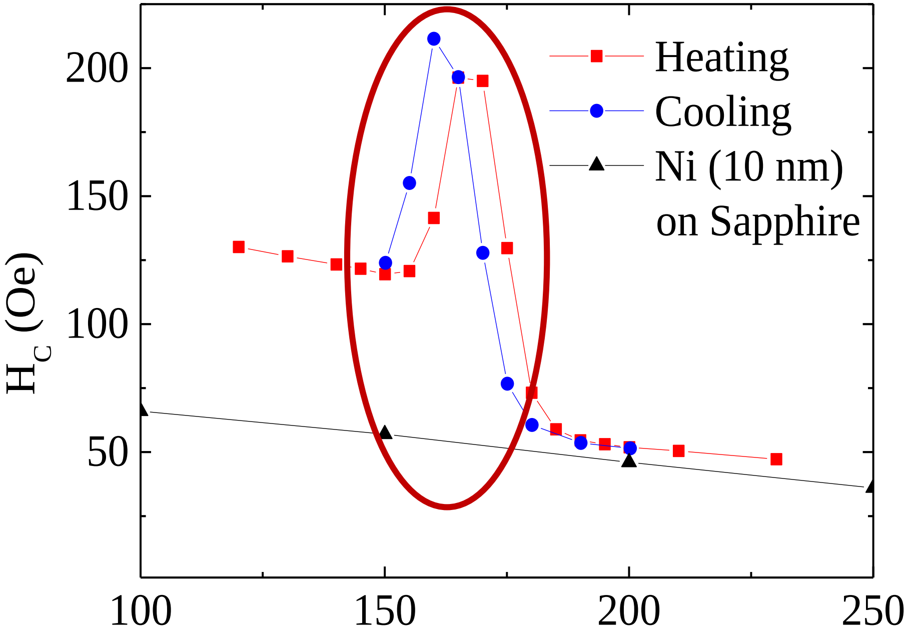
V_2O_3/Ni


Nb Capping Layer (5 nm)
Ni (10 nm)
V_2O_3 (100 nm)
Sapphire

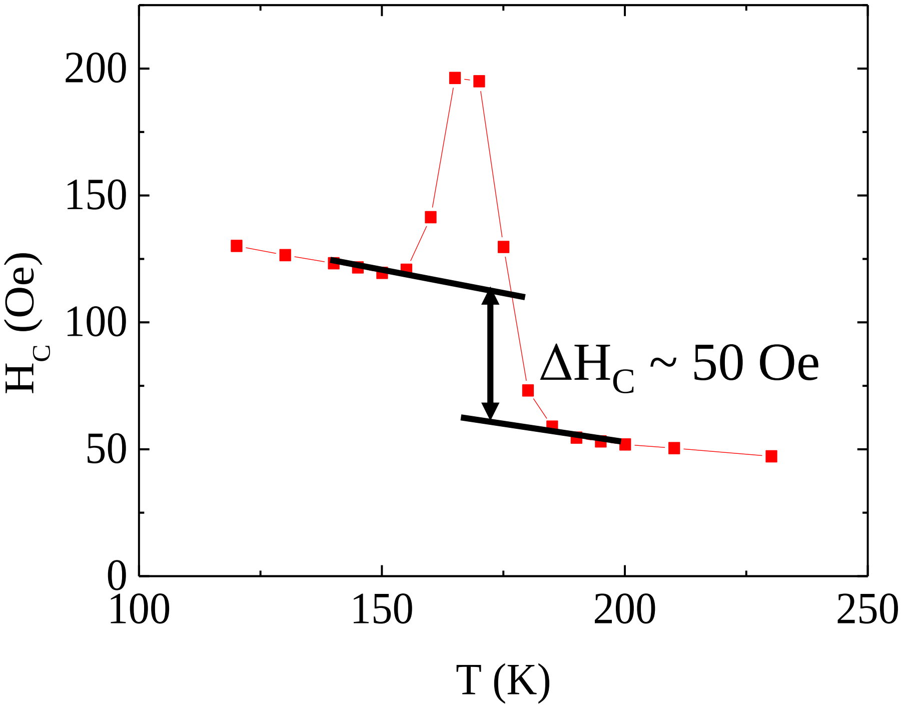
Peak at T_C = 150 – 165 K!

Coercivity Enhancement





Coercivity Enhancement



Structural Phase Transition in V_2O_3

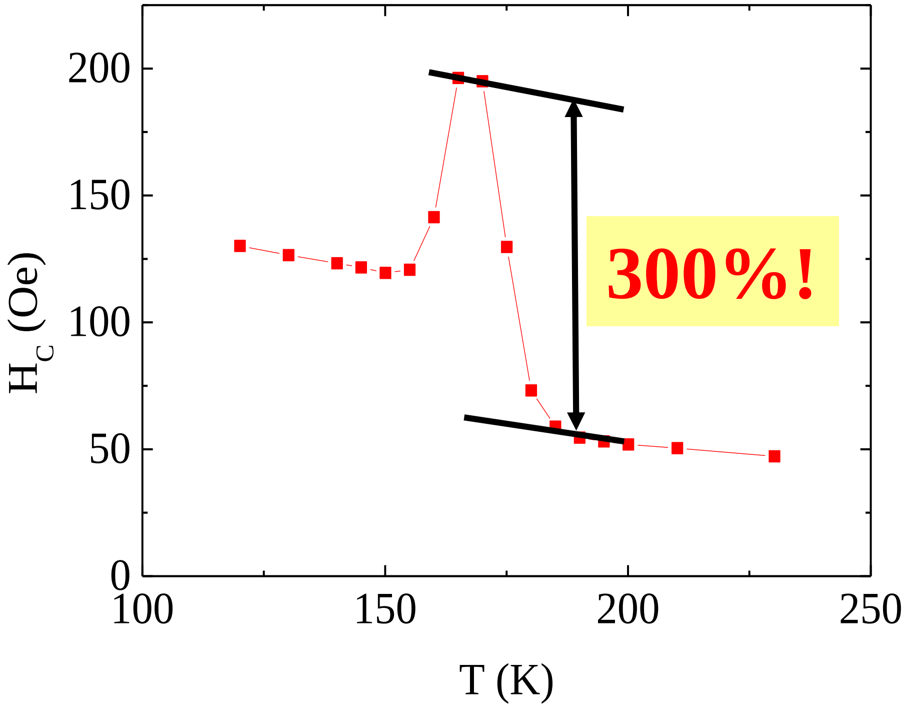
Stress in Ni ~ 10’s of MPa

Stress Anisotropy Field ~ 50 Oe

J. de la Venta, S. Wang, J. G. Ramirez, and I. K. Schuller, Appl. Phys. Lett. **102**, 122404 (2013)

Coercivity Enhancement

What Reaches Maximum at T = 165 K in V_2O_3?



H_C Reaches Maximum at T = 165 K

⬇

Phase Coexistence in V_2O_3

⬇

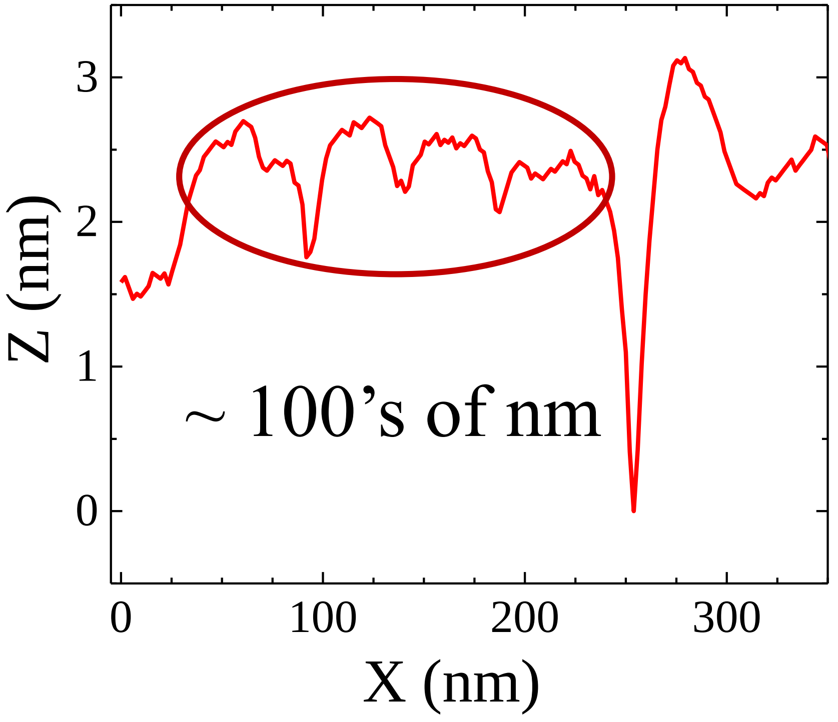
Single Phase Domain
$\lambda_{V_2O_3} \leq 100$ nm

A. S. McLeod *et al.*, J49.00011, Cryogenic Infrared Nano-Imaging of the Metal-Insulator Transition in V_2O_3, APS March Meeting, 2014

Competing Length Scales

Surface Morphology

Terraces



Magnetic Domain d_{Ni} > 100 nm

Single Phase Domain $\lambda_{V_2O_3} \leq 100$ nm

$d_{Ni} > \lambda_{V_2O_3}$

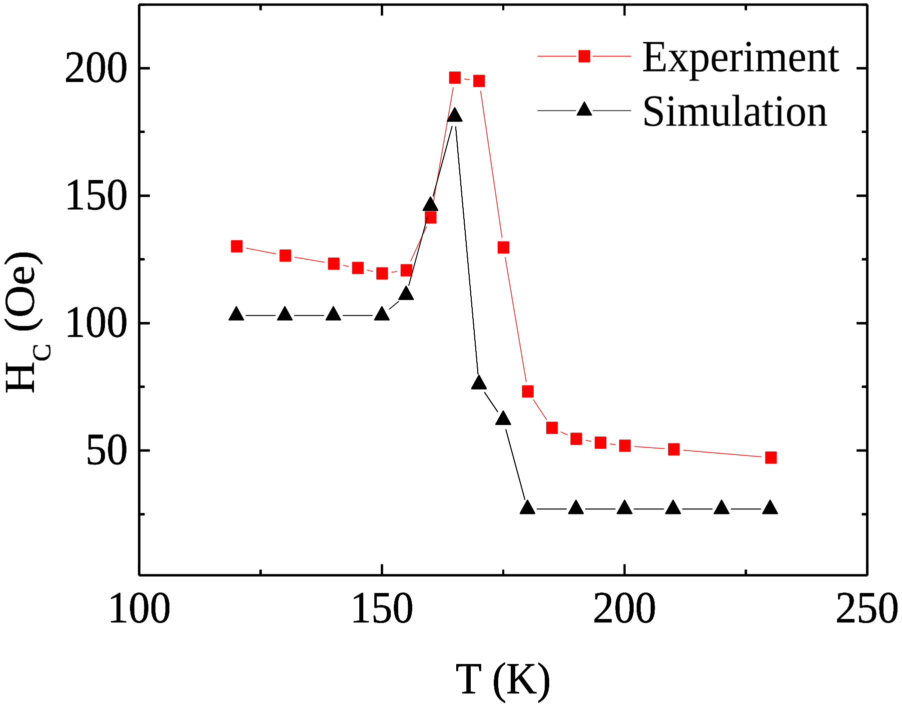
Phase Coexistence of V_2O_3

T-dependent Disorder

Enhanced Coercivity

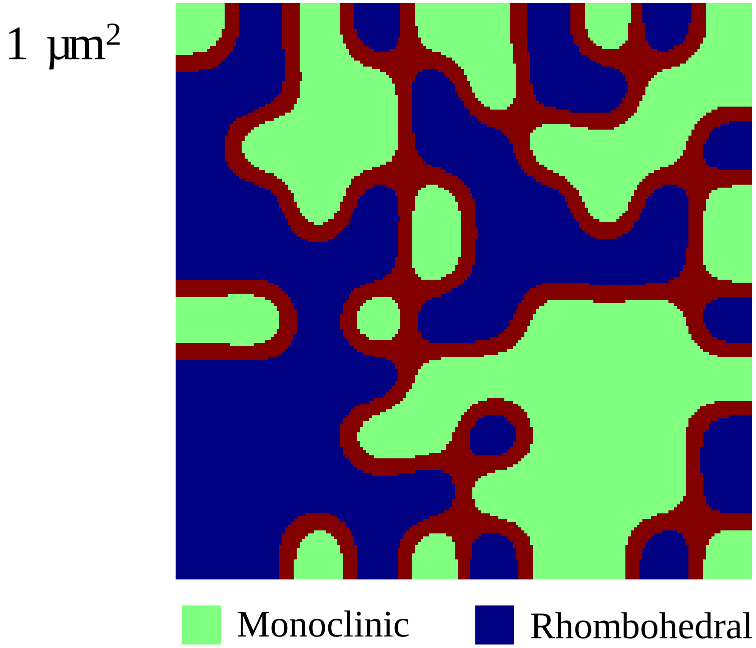
Micromagnetic Simulation

Ni



V_2O_3: $\lambda_{V_2O_3} = 100$ nm

T = 165 K



$K_{Stress} = 1 \times 10^4$ J/m³ $K_{Pin} = 4 \times 10^4$ J/m³ **25 – 30 nm Boundary**

Gaussian Distribution of T_C

T_C(Mean) = 165 K

OOMMF, NIST

Magnetization Reversal

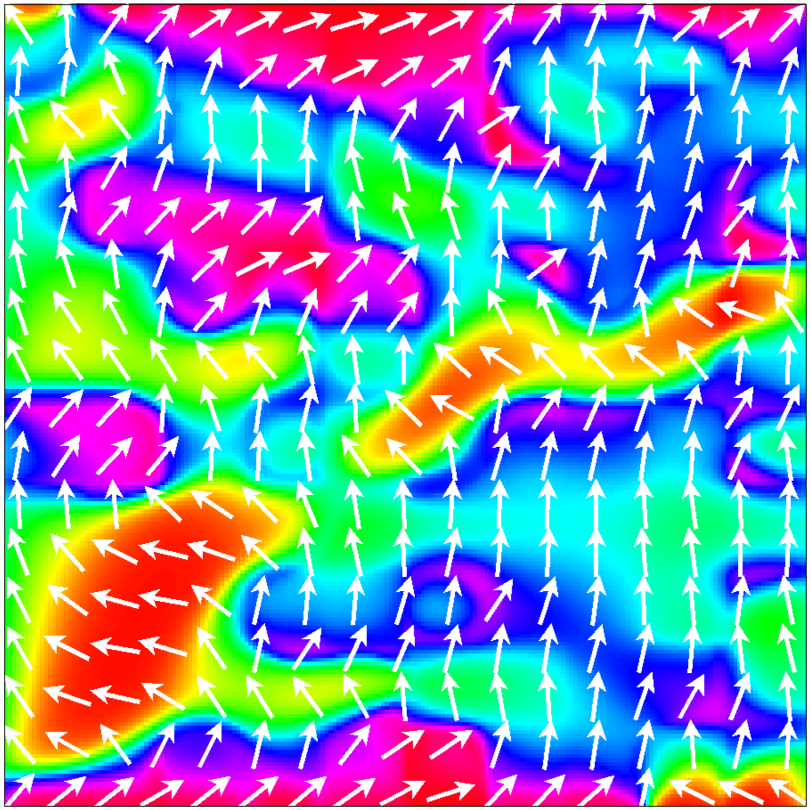
1 μm^2

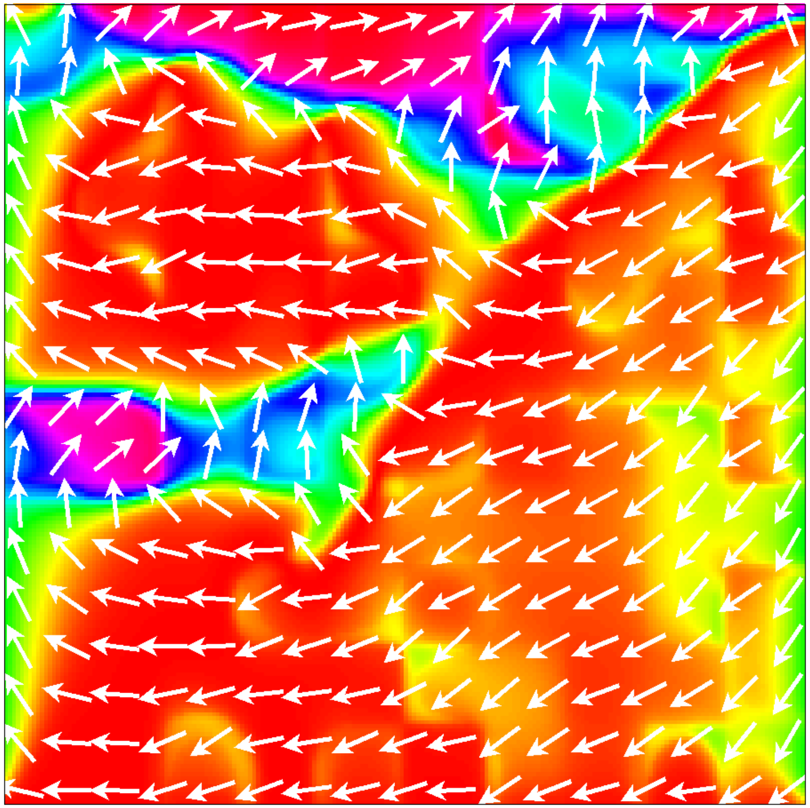
165 K

Before H_C

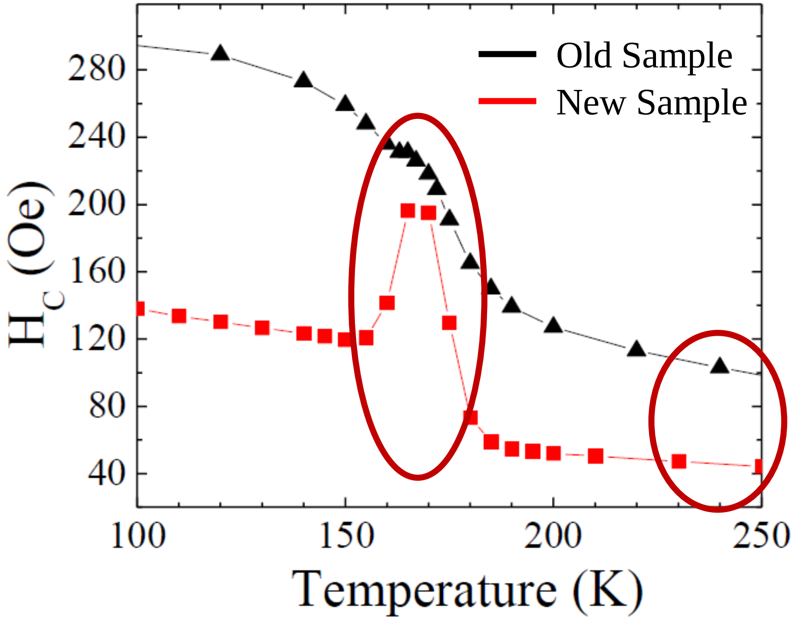
H ↔

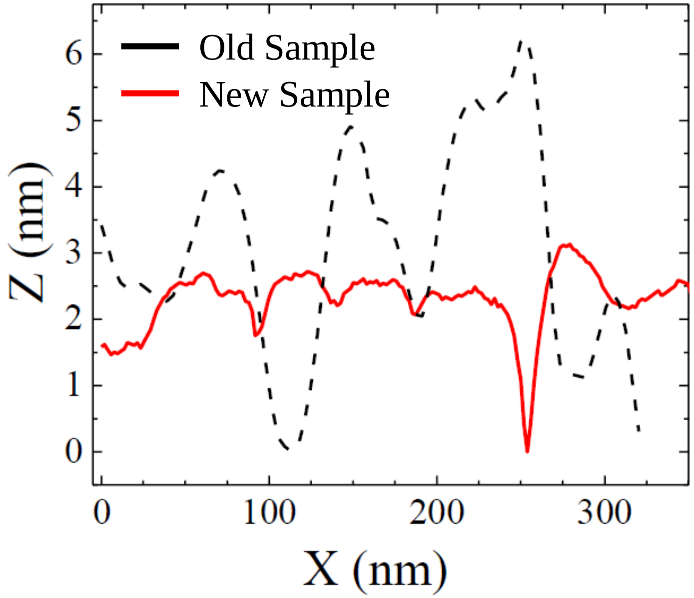
After H_C





Microstructure Comparison





New Sample: 100’s of nm Terraces (< 1 nm)

⬇

$d_{Ni} > 100$ nm

⬇

$d_{Ni} > \lambda_{V_2O_3}$, Enhancement

Old Sample: Higher Roughness (> 3 nm)

⬇

$d_{Ni} \sim 50 – 100$ nm

⬇

$d_{Ni} \approx \lambda_{V_2O_3}$, No Enhancement

Coercivity Enhancement in V_2O_3/Ni

- Magnetic Measurement – **Enhanced Coercivity** in V_2O_3/Ni
- Microstructure – **Competing Length Scales (d_{Ni} vs. $\lambda_{V_2O_3}$)**
- Model – **Phase Coexistence** Induced Pinning
- Simulation – **Quantitatively Reproduce** Enhanced Coercivity

J. de la Venta, S. Wang, T. Saerbeck, J. G. Ram ŕez, I. Valmianski, and Ivan K. Schuller, Appl. Phys. Lett. **104**, 062410 (2014)
T. Saerbeck, J. de la Venta, S. Wang, J. G. Ramirez, M. Erekhinsky, I. Valmianski, I. K. Schuller, J. Mater. Res., Invited Review (2014)

Summary

- First Order SPT – **Large Stress within a Narrow Temperature Range**
- Multiple Driving Forces to Induce SPT – **Temperature, Voltage/Current, Light, Gating, Pressure and etc.**
- Multiple Tuning Parameters – **Different FMs & Deposition Conditions**
- Competing Length Scales – **Disorder due to Nanoscale Inhomogeneity**

Outlook

- Probe V_2O_3 Domain – **Scanning Near-Field Optical Microscopy (SNOM)**
- Probe Magnetic Domain in Ni – **Neutron Scattering**
- Coercivity Enhancement with VO_2 – **Smooth Surface** (TiO_2 or MgF_2 Substrate)
- Dynamics (FMR) – **Damping Divergence due to Nanoscale Disorder**

swang@physics.ucsd.edu
http://www.linkedin.com/pub/siming-wang/42/935/595